## SQ7414CENW

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Vishay Siliconix

# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

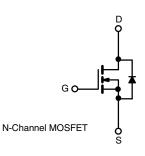


Marking Code: Q037

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	60				
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.023				
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.028				
I <sub>D</sub> (A)	18				
Configuration	Single				
Package	PowerPAK 1212-8W				

#### FEATURES

- TrenchFET<sup>®</sup> power MOSFET
- Low thermal resistance PowerPAK<sup>®</sup> 1212-8 package with 1.07 mm profile
- PWM optimized
- 100 % R<sub>g</sub> and UIS tested
- AEC-Q101 qualified
- Wettable flank terminals
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25	°C, unless otherw	rise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	60	v
Gate-source voltage		V <sub>GS</sub>	± 20	v
Continuous drain current <sup>a</sup>	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	18	
Continuous drain current "	T <sub>C</sub> = 125 °C		18	
Continuous source current (diode conduction) a		I <sub>S</sub>	18	A
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	72	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	20	
Single pulse avalanche energy	L = 0.1 MH	E <sub>AS</sub>	16	mJ
Maximum neuror discipation b	T <sub>C</sub> = 25 °C		62	w
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C		20	vv
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temperature) d			260	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount <sup>c</sup>	R <sub>thJA</sub>	81	°C/W	
Junction-to-case (drain)		R <sub>thJC</sub>	2.4	0/10	

Notes

a. Package limited

- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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RoHS

COMPLIANT HALOGEN

FREE

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SPECIFICATIONS (T <sub>C</sub> = 25 °C	, unless otherv	vise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static					•		
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> =	= 0 V, I <sub>D</sub> = 250 μA	60	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μΑ	1.5	2	2.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	150	1
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	20	-	-	Α
		$V_{GS} = 10 V$	I <sub>D</sub> = 8.7 A	-	0.016	0.023	
Drain courses on state resistance a	Б	$V_{GS} = 10 V$	I <sub>D</sub> = 8.7 A, T <sub>J</sub> = 125 °C	-	-	0.039	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 V$	I <sub>D</sub> = 8.7 A, T <sub>J</sub> = 175 °C	-	-	0.050	Ω
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 8.7 A	-	0.019	0.028	
Forward transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 8.7 A	-	50	-	S
Dynamic <sup>b</sup>	•	•		•	•	•	
Input capacitance	C <sub>iss</sub>			-	1275	1590	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V, f = 1 MHz	-	112	140	pF
Reverse transfer capacitance	C <sub>rss</sub>			-	42	52	
Total gate charge <sup>c</sup>	Qg			-	19	25	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 8.7 \text{ A}$	-	2.6	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	3.6	-	
Gate resistance	Rg		f = 1 MHz	0.6	1.12	1.6	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	8	10	
Rise time <sup>c</sup>	t <sub>r</sub>		= 30 V, $R_{L}$ = 30 $\Omega$	-	13	16	1
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 1$ Å, $V_{GEN} = 10$ V, $R_g = 1$ $\Omega$		-	22	26	- ns
Fall time <sup>c</sup>	t <sub>f</sub>			-	15	18	
Source-Drain Diode Ratings and Cha	racteristics b						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	72	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> =	8.7 A, V <sub>GS</sub> = 0 V	-	0.8	1.2	V

Notes

a. Pulse test; pulse width  $\leq 300~\mu\text{s},\,duty~cycle \leq 2~\%$ 

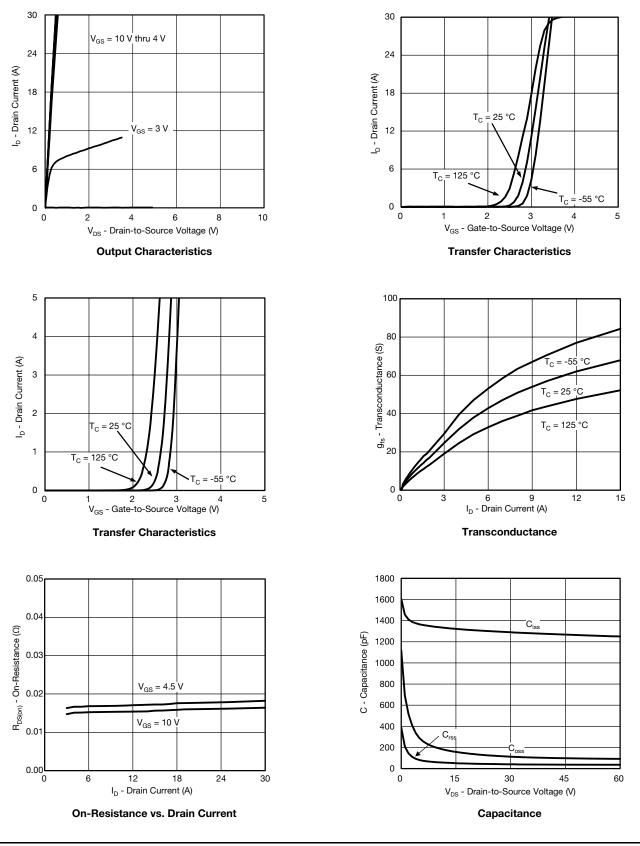
b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



S17-1695-Rev. A, 13-Nov-17

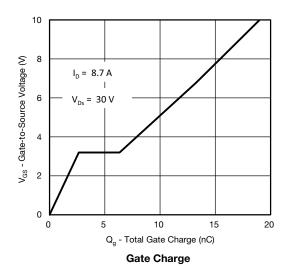
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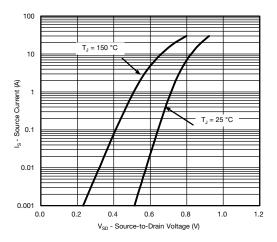
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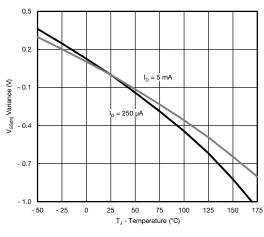


### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

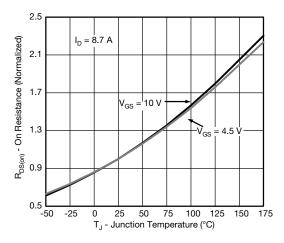




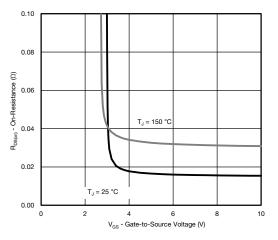
Source Drain Diode Forward Voltage



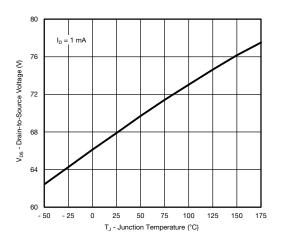
**Threshold Voltage** 



**On-Resistance vs. Junction Temperature** 



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

S17-1695-Rev. A, 13-Nov-17

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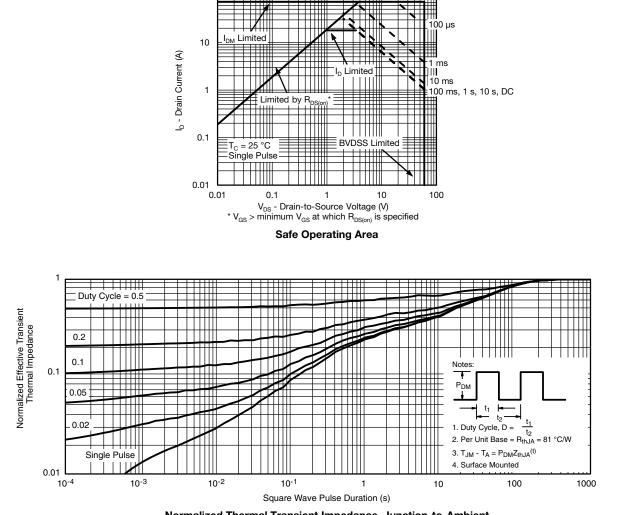


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## **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

100

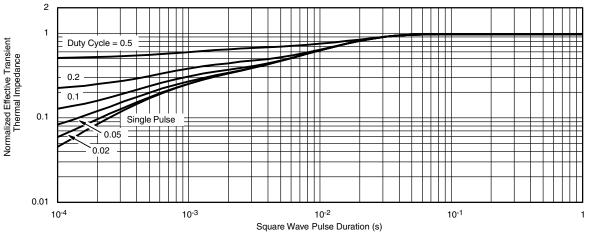


Normalized Thermal Transient Impedance, Junction-to-Ambient



Document Number: 75674

### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

The characteristics shown in the two graphs

S17-1695-Rev. A, 13-Nov-17

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

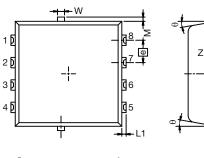
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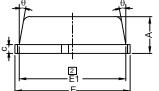


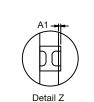
# PowerPAK<sup>®</sup> 1212-8W Case Outline

Δ2

224



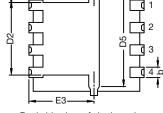




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Б



E2

E4

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Notes
1 Inch will govern

 Dimensions exclusive of mold gate burrs
 Dimensions exclusive of mold flash and cutting burrs

DIM.	MILLIMETERS			INCHES				
DIM.	MIN.	NOM.	MAX.	MIN.	MIN. NOM.			
А	0.97	1.04	1.12	0.038	0.041	0.044		
A1	0	-	0.05	0	-	0.002		
A2	0	-	0.13	0	-	0.005		
b	0.23	0.30	0.41	0.009	0.012	0.016		
С	0.23	0.28	0.33	0.009	0.011	0.013		
D	3.20	3.30	3.40	0.126	0.130	0.134		
D1	2.95	3.05	3.15	0.116	0.120	0.124		
D2	1.98	2.11	2.24	0.078	0.083	0.088		
D4	0.47 typ.			0.0185 typ.				
D5	2.3 typ.			0.090 typ.				
E	3.20	3.30	3.40	0.126	0.130	0.134		
E1	2.95	3.05	3.15	0.116	0.120	0.124		
E2	1.47	1.60	1.73	0.058	0.063	0.068		
E3	1.75	1.85	1.98	0.069	0.073	0.078		
E4		0.34 typ.		0.013 typ.				
е		0.65 BSC.		0.026 BSC				
К		0.86 typ.		0.034 typ.				
Н	0.30	0.41	0.51	0.012	0.016	0.020		
L	0.30	0.43	0.56	0.012	0.017	0.022		
L1	0.06	0.13	0.20	0.002	0.005	0.008		
θ	0°	-	12°	0°	-	12°		
W	0.15	0.25	0.36	0.006	0.010	0.014		
М	0.125 typ.			0.005 typ.				
N: C15-1530-R	ev. B, 16-Nov-15							

Backside view of single pad



## RECOMMENDED MINIMUM PADS FOR PowerPAK<sup>®</sup> 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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